Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

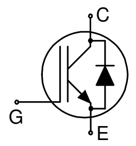
With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

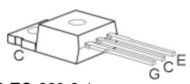
We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

Fast IGBT in NPT-technology with soft, fast recovery anti-parallel Emitter Controlled Diode





PG-TO-220-3-1
(TO-220AB)

Allowed number of short circuits: <1000; time between short circuits: >1s.

- 40lower E_{off} compared to previous generation
- Short circuit withstand time – 10 µs
- Designed for:
  - Motor controls
  - Inverter
  - SMPS
- NPT-Technology offers:
  - very tight parameter distribution
  - high ruggedness, temperature stable behaviour
  - parallel switching capability
- Qualified according to JEDEC[1] for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : http://www.infineon.com/igbt/

Type	V_{CE}	I_C	E_{off}	T_j	Marking	Package
SKP02N120	1200V	2A	0.11mJ	150°C	K02N120	PG-TO-220-3-1

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	1200	V
DC collector current	I_C		A
T_C = 25°C		6.2	
T_C = 100°C		2.8	
Pulsed collector current, t_p limited by T_{jmax}	I_{Cpuls}	9.6	
Turn off safe operating area $V_{CE} \leq$ 1200V, $T_j \leq$ 150°C	-	9.6	
Diode forward current	I_F		
T_C = 25°C		4.5	
T_C = 100°C		2	
Diode pulsed current, t_p limited by T_{jmax}	I_{Fpuls}	9	
Gate-emitter voltage	V_{GE}	±20	V
Short circuit withstand time[2] V_{GE} = 15V, 100V$\leq V_{CC} \leq$1200V, $T_j \leq$ 150°C	t_{SC}	10	µs
Power dissipation T_C = 25°C	P_{tot}	62	W
Operating junction and storage temperature	T_j , T_{stg}	-55...+150	°C
Soldering temperature, wavesoldering, 1.6mm (0.063 in.) from case for 10s	T_s	260	

[1] J-STD-020 and JESD-022
[2] Allowed number of short circuits: <1000; time between short circuits: >1s.

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}		2.0	K/W
Diode thermal resistance, junction – case	R_{thJCD}		4.5	
Thermal resistance, junction – ambient	R_{thJA}		62	

Electrical Characteristic, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	V_{GE}=0V, I_C=100µA	1200	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	V_{GE} = 15V, I_C=2A T_j=25°C T_j=150°C	 2.5 -	 3.1 3.7	 3.6 4.3	
Diode forward voltage	V_F	V_{GE}=0V, I_F=2A T_j=25°C T_j=150°C	 -	 2.0 1.75	 2.5 	
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C=100µA, V_{CE}=V_{GE}	3	4	5	
Zero gate voltage collector current	I_{CES}	V_{CE}=1200V, V_{GE}=0V T_j=25°C T_j=150°C	 - -	 - -	 25 100	µA
Gate-emitter leakage current	I_{GES}	V_{CE}=0V, V_{GE}=20V	-	-	100	nA
Transconductance	g_{fs}	V_{CE}=20V, I_C=2A		1.5	-	S
Dynamic Characteristic						
Input capacitance	C_{iss}	V_{CE}=25V, V_{GE}=0V, f=1MHz	-	205	250	pF
Output capacitance	C_{oss}		-	28	34	
Reverse transfer capacitance	C_{rss}		-	12	15	
Gate charge	Q_{Gate}	V_{CC}=960V, I_C=2A V_{GE}=15V	-	11	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	7	-	nH
Short circuit collector current[2)]	$I_{C(SC)}$	V_{GE}=15V, t_{SC}≤10µs 100V≤V_{CC}≤1200V, T_j ≤ 150°C	-	24	-	A

[2)] Allowed number of short circuits: <1000; time between short circuits: >1s.

Switching Characteristic, Inductive Load, at T_j=25 °C

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_j=25°C, V_{CC}=800V, I_C=2A, V_{GE}=15V/0V, R_G=91Ω, L_σ[1)]=180nH, C_σ[1)]=40pF Energy losses include "tail" and diode reverse recovery.	-	23	30	ns
Rise time	t_r		-	16	21	
Turn-off delay time	$t_{d(off)}$		-	260	340	
Fall time	t_f		-	61	80	
Turn-on energy	E_{on}		-	0.16	0.21	mJ
Turn-off energy	E_{off}		-	0.06	0.08	
Total switching energy	E_{ts}		-	0.22	0.29	
Anti-Parallel Diode Characteristic						
Diode reverse recovery time	t_{rr} t_S t_F	T_j=25°C, V_R=800V, I_F=2A, di_F/dt=250A/µs	- - -	50		ns
Diode reverse recovery charge	Q_{rr}		-	0.10		µC
Diode peak reverse recovery current	I_{rrm}		-	4.2		A
Diode peak rate of fall of reverse recovery current during t_F	di_{rr}/dt		-	400		A/µs

Switching Characteristic, Inductive Load, at T_j=150 °C

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_j=150°C V_{CC}=800V, I_C=2A, V_{GE}=15V/0V, R_G=91Ω, L_σ[1)]=180nH, C_σ[1)]=40pF Energy losses include "tail" and diode reverse recovery.	-	26	31	ns
Rise time	t_r		-	14	17	
Turn-off delay time	$t_{d(off)}$		-	290	350	
Fall time	t_f		-	85	102	
Turn-on energy	E_{on}		-	0.27	0.33	mJ
Turn-off energy	E_{off}		-	0.11	0.15	
Total switching energy	E_{ts}		-	0.38	0.48	
Anti-Parallel Diode Characteristic						
Diode reverse recovery time	t_{rr} t_S t_F	T_j=150°C V_R=800V, I_F=2A, di_F/dt=300A/µs	- - -	90		ns
Diode reverse recovery charge	Q_{rr}		-	0.30		µC
Diode peak reverse recovery current	I_{rrm}		-	6.7		A
Diode peak rate of fall of reverse recovery current during t_F	di_{rr}/dt		-	110		A/µs

[1)] Leakage inductance L_σ and stray capacity C_σ due to dynamic test circuit in figure E.

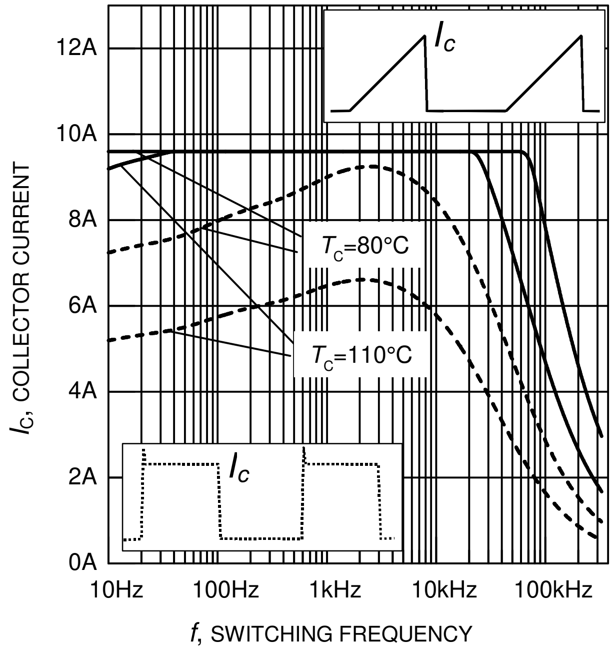


Figure 1. Collector current as a function of switching frequency
($T_j \leq 150°C$, $D = 0.5$, $V_{CE} = 800V$, $V_{GE} = +15V/0V$, $R_G = 91\Omega$)

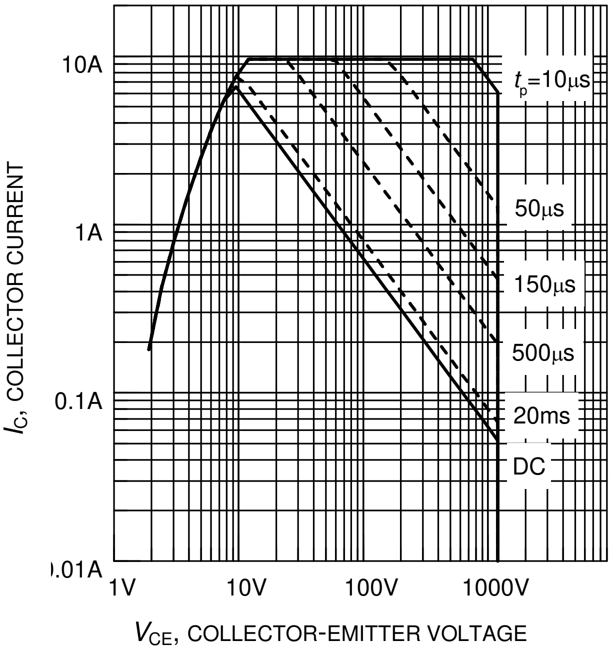


Figure 2. Safe operating area
($D = 0$, $T_C = 25°C$, $T_j \leq 150°C$)

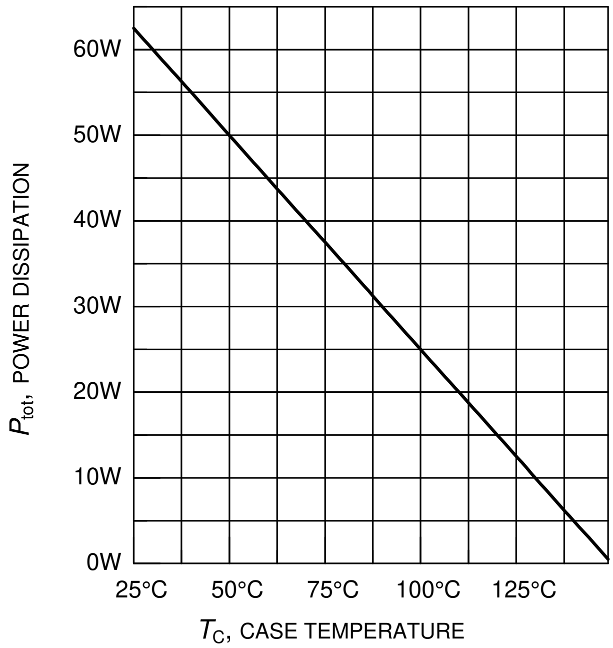


Figure 3. Power dissipation as a function of case temperature
($T_j \leq 150°C$)

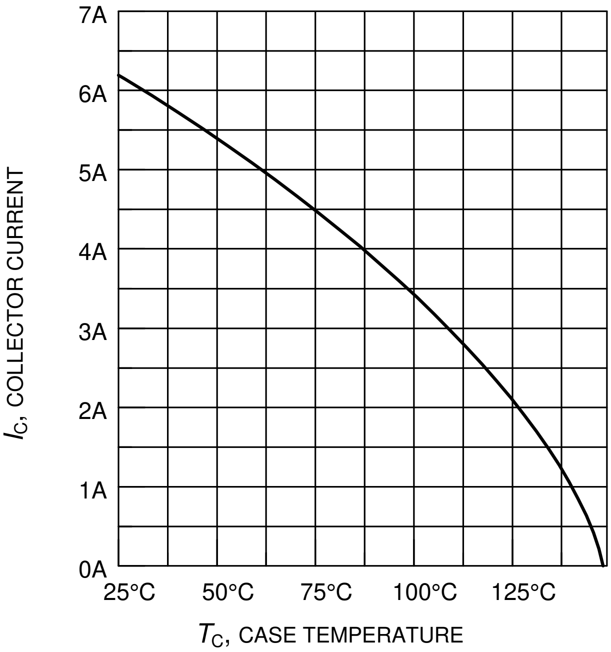


Figure 4. Collector current as a function of case temperature
($V_{GE} \leq 15V$, $T_j \leq 150°C$)

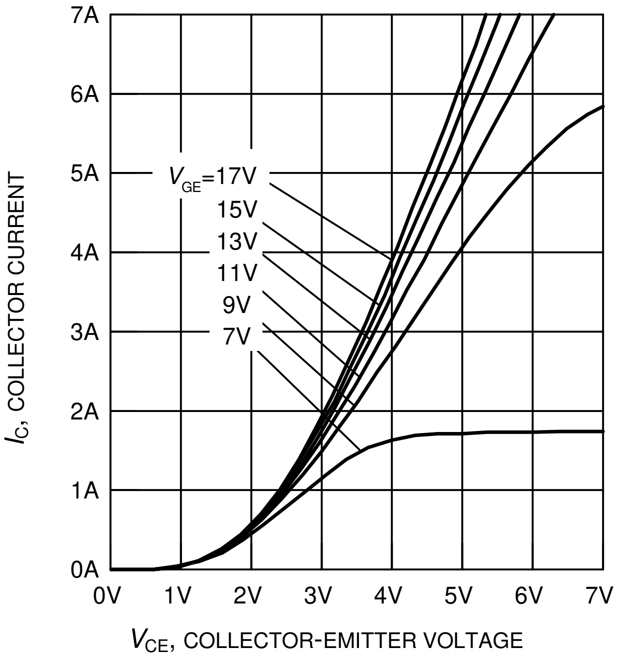


Figure 5. Typical output characteristics
(T_j = 25°C)

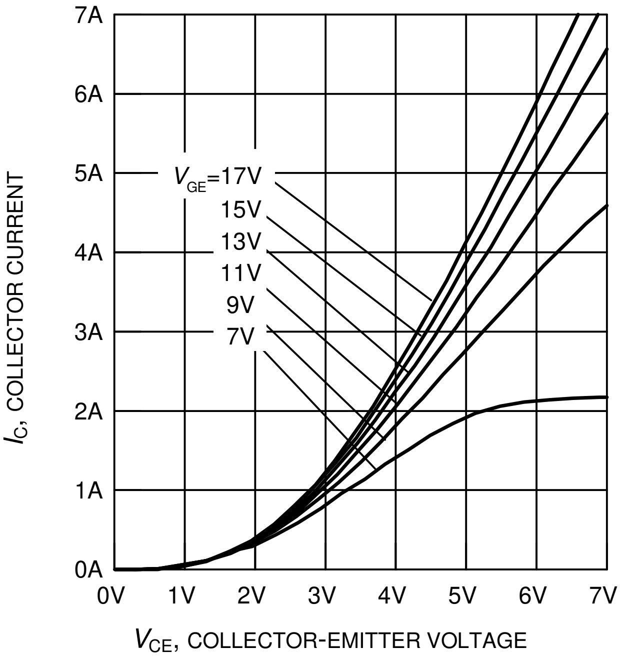


Figure 6. Typical output characteristics
(T_j = 150°C)

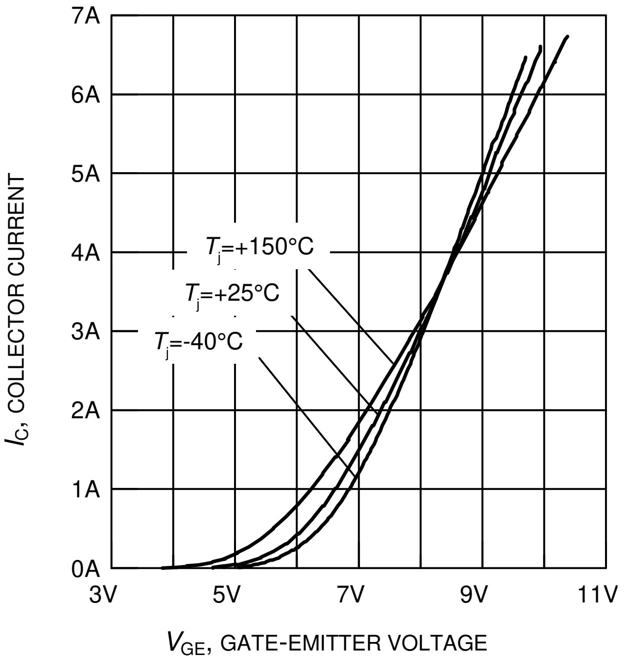


Figure 7. Typical transfer characteristics
(V_{CE} = 20V)

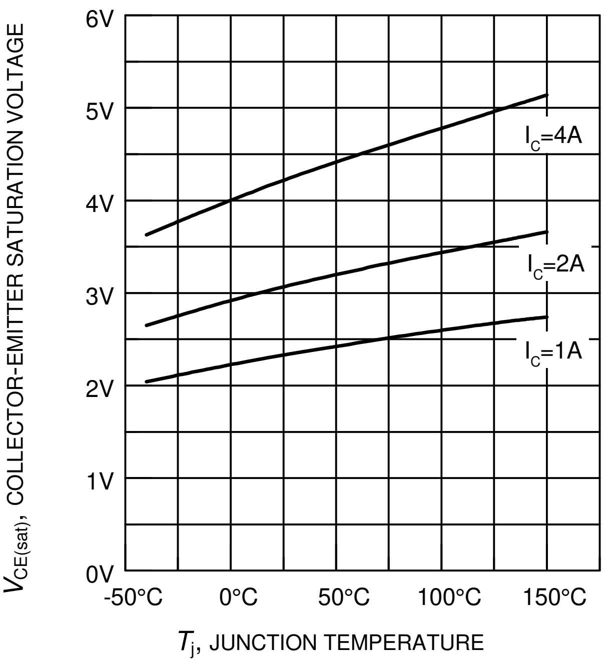


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
(V_{GE} = 15V)

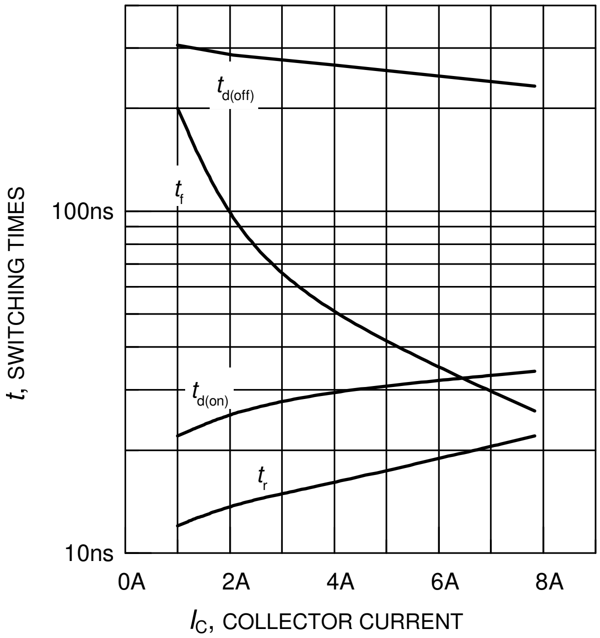


Figure 9. Typical switching times as a function of collector current
(inductive load, T_j = 150°C,
V_{CE} = 800V, V_{GE} = +15V/0V, R_G = 91Ω,
dynamic test circuit in Fig.E)

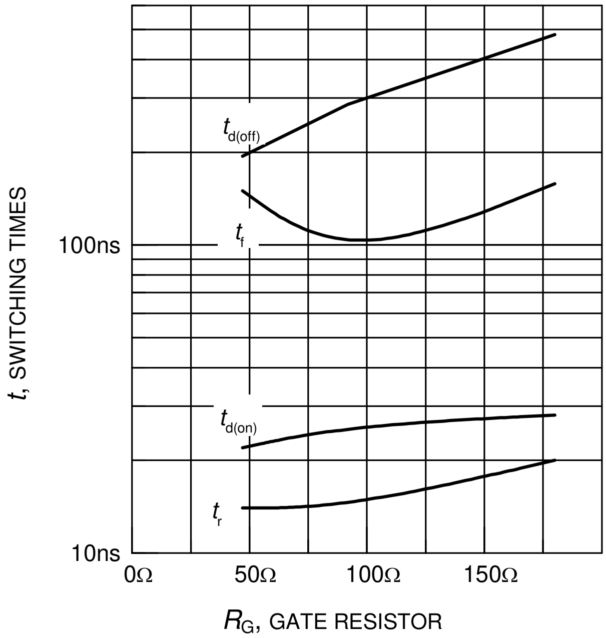


Figure 10. Typical switching times as a function of gate resistor
(inductive load, T_j = 150°C,
V_{CE} = 800V, V_{GE} = +15V/0V, I_C = 2A,
dynamic test circuit in Fig.E)

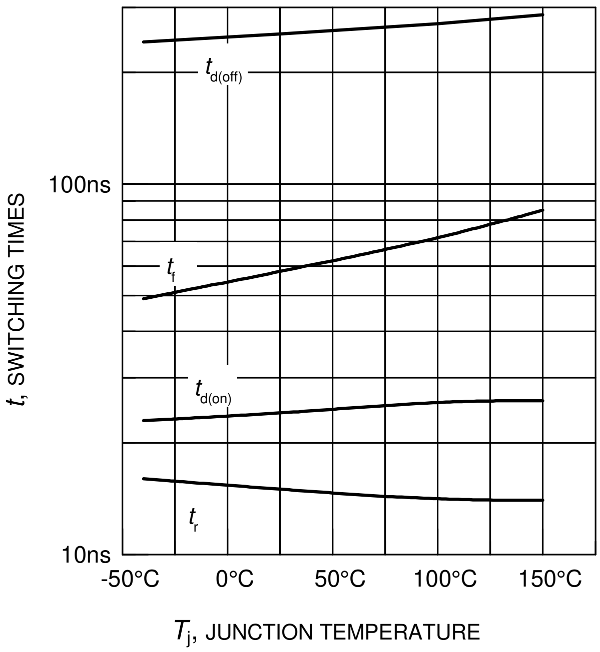


Figure 11. Typical switching times as a function of junction temperature
(inductive load, V_{CE} = 800V,
V_{GE} = +15V/0V, I_C = 2A, R_G = 91Ω,
dynamic test circuit in Fig.E)

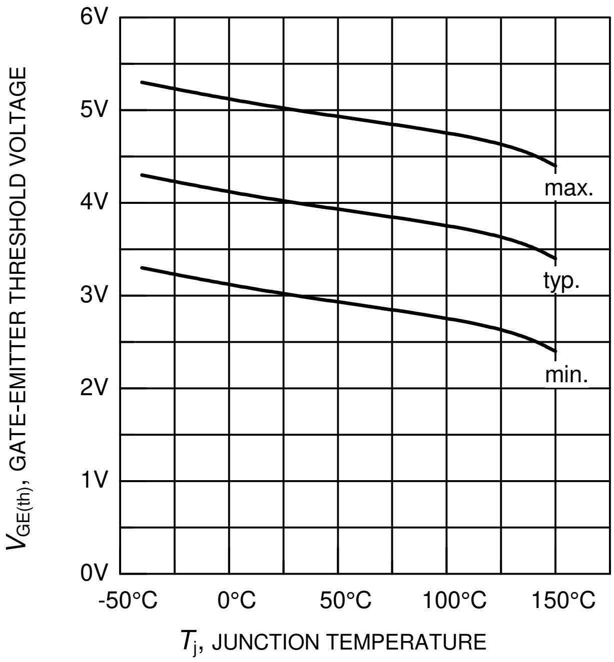


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
(I_C = 0.3mA)

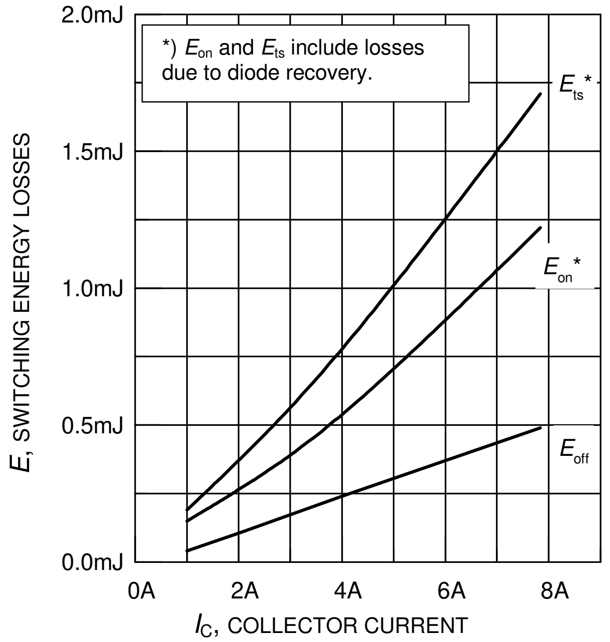


Figure 13. Typical switching energy losses as a function of collector current
(inductive load, T_j = 150°C,
V_{CE} = 800V, V_{GE} = +15V/0V, R_G = 91Ω,
dynamic test circuit in Fig.E)

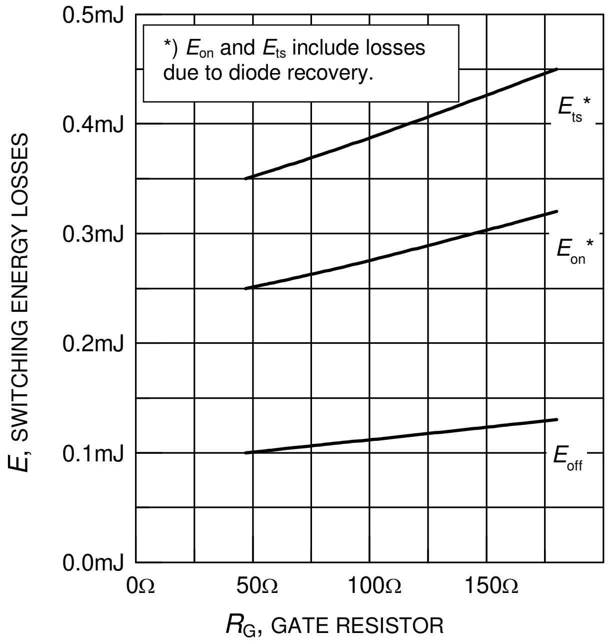


Figure 14. Typical switching energy losses as a function of gate resistor
(inductive load, T_j = 150°C,
V_{CE} = 800V, V_{GE} = +15V/0V, I_C = 2A,
dynamic test circuit in Fig.E)

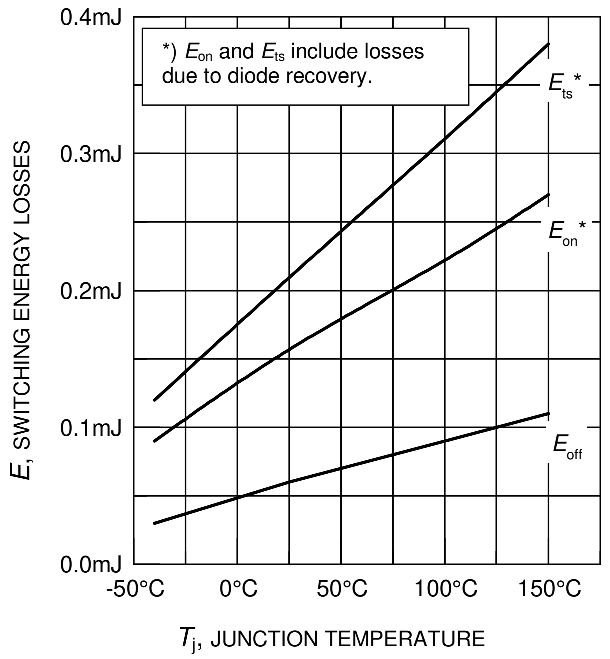


Figure 15. Typical switching energy losses as a function of junction temperature
(inductive load, V_{CE} = 800V,
V_{GE} = +15V/0V, I_C = 2A, R_G = 91Ω,
dynamic test circuit in Fig.E)

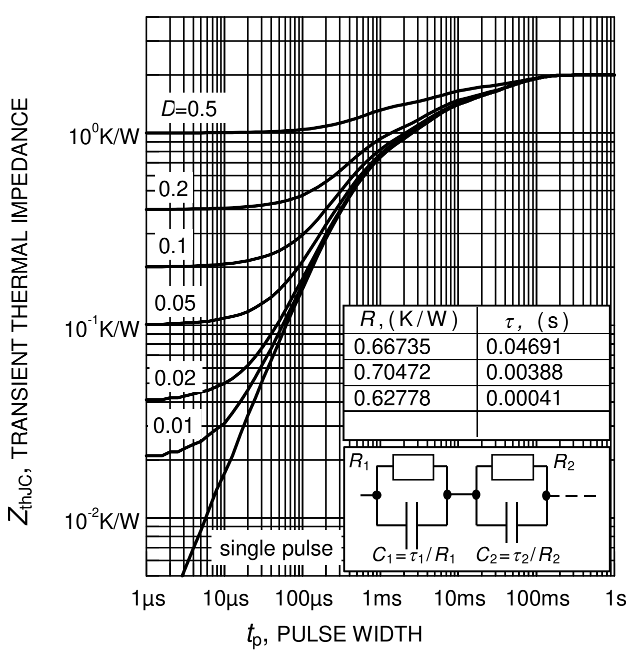


Figure 16. IGBT transient thermal impedance as a function of pulse width
($D = t_p / T$)

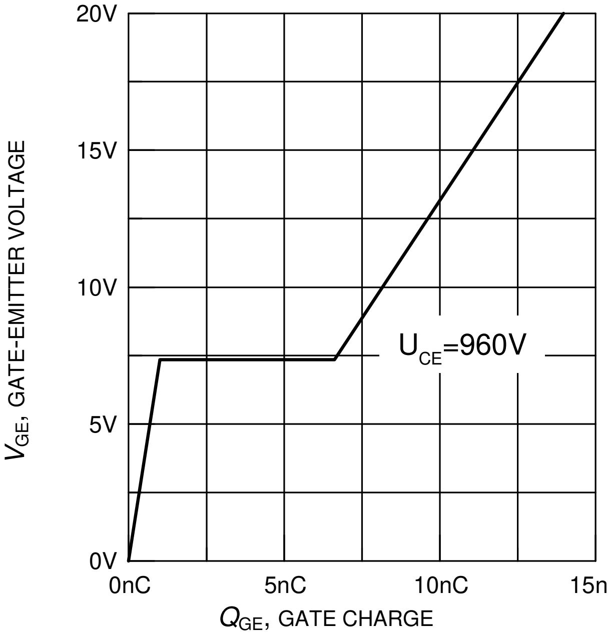


Figure 17. Typical gate charge
(I_C = 2A)

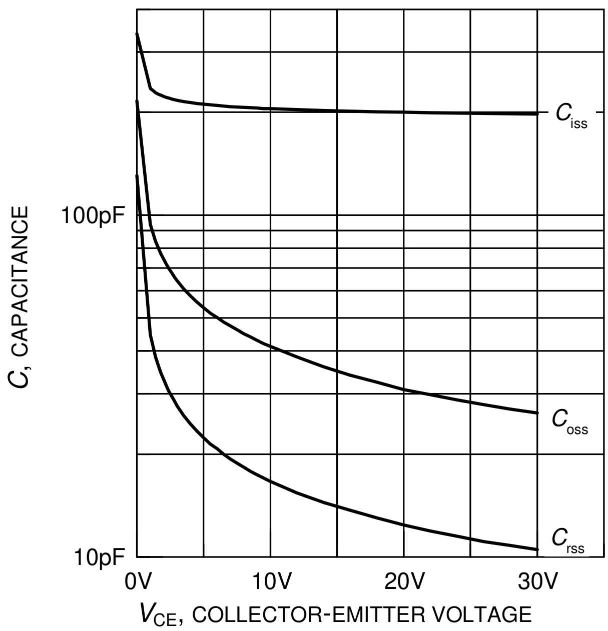


Figure 18. Typical capacitance as a function of collector-emitter voltage
(V_{GE} = 0V, f = 1MHz)

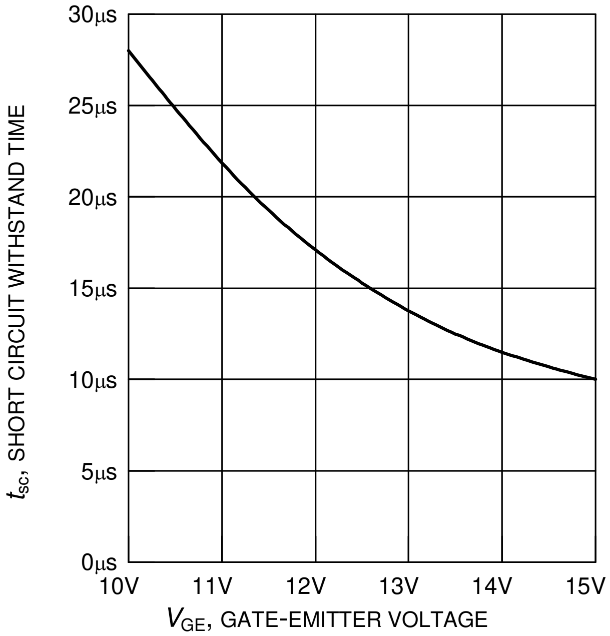


Figure 19. Short circuit withstand time as a function of gate-emitter voltage
(V_{CE} = 1200V, start at T_j = 25°C)

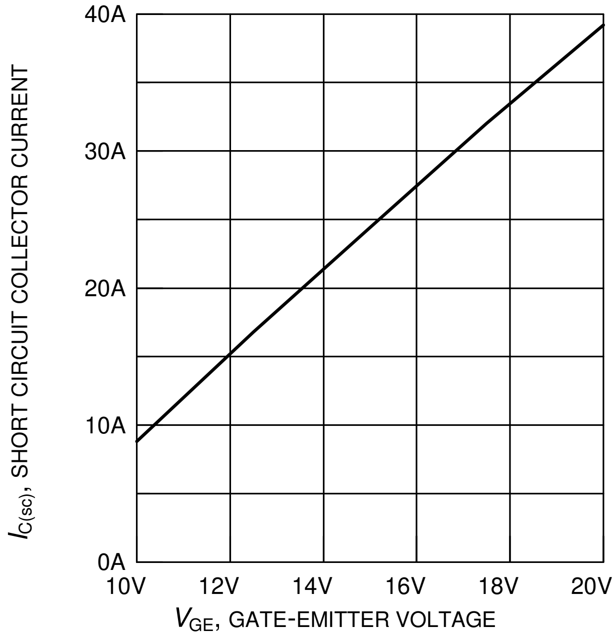


Figure 20. Typical short circuit collector current as a function of gate-emitter voltage
(100V≤V_{CE} ≤1200V, T_C = 25°C, T_j ≤ 150°C)

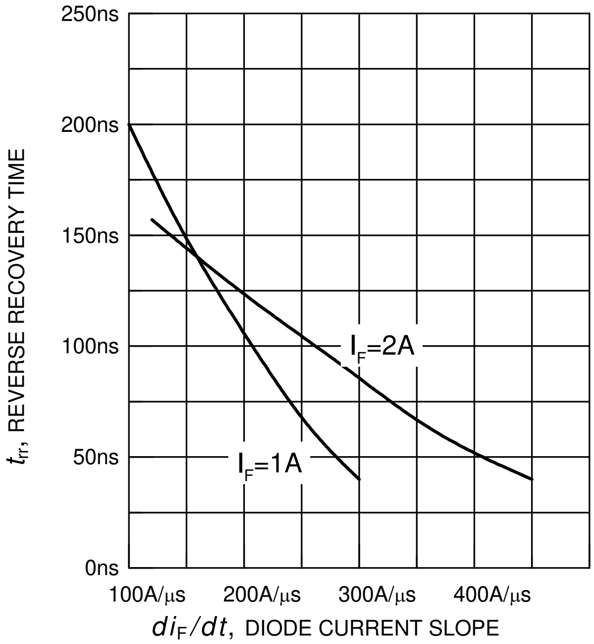


Figure 21. Typical reverse recovery time as a function of diode current slope
(V_R = 800V, T_j = 150°C,
dynamic test circuit in Fig.E)

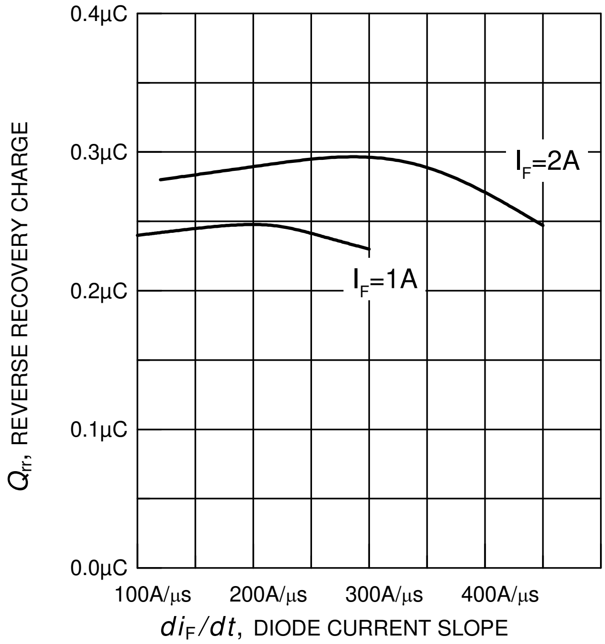


Figure 22. Typical reverse recovery charge as a function of diode current slope
(V_R = 800V, T_j = 150°C,
dynamic test circuit in Fig.E)

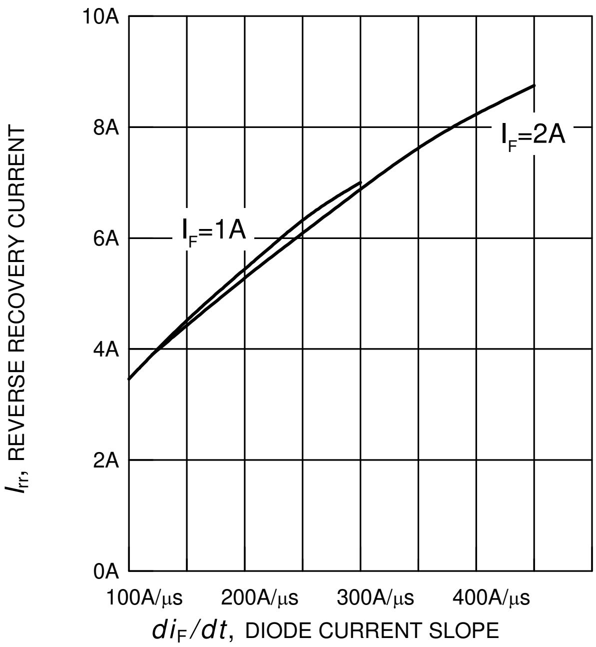


Figure 23. Typical reverse recovery current as a function of diode current slope
(V_R = 800V, T_j = 150°C,
dynamic test circuit in Fig.E)

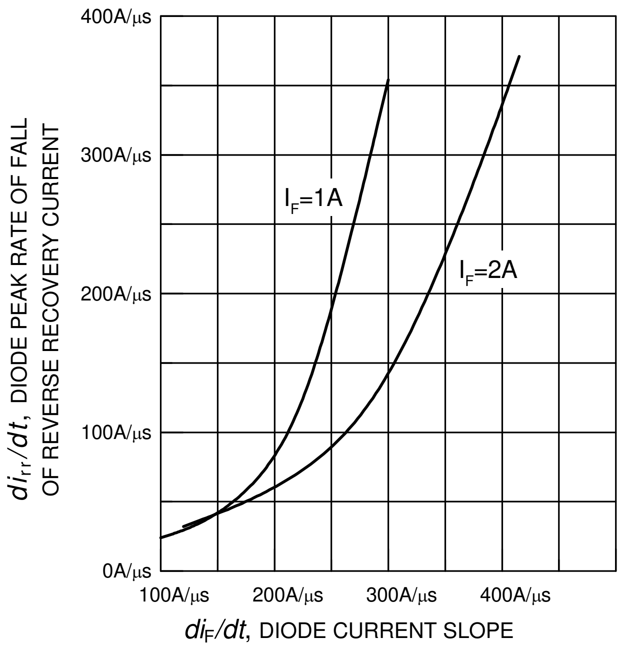


Figure 24. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope
(V_R = 800V, T_j = 150°C,
dynamic test circuit in Fig.E)

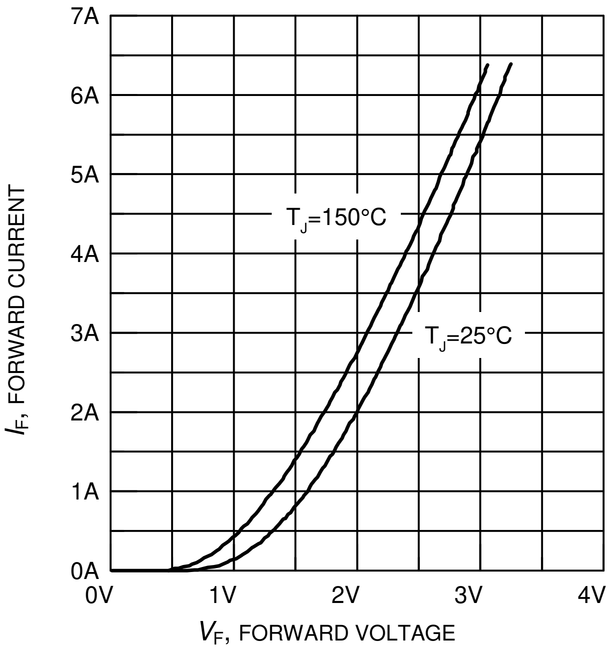


Figure 25. Typical diode forward current as a function of forward voltage

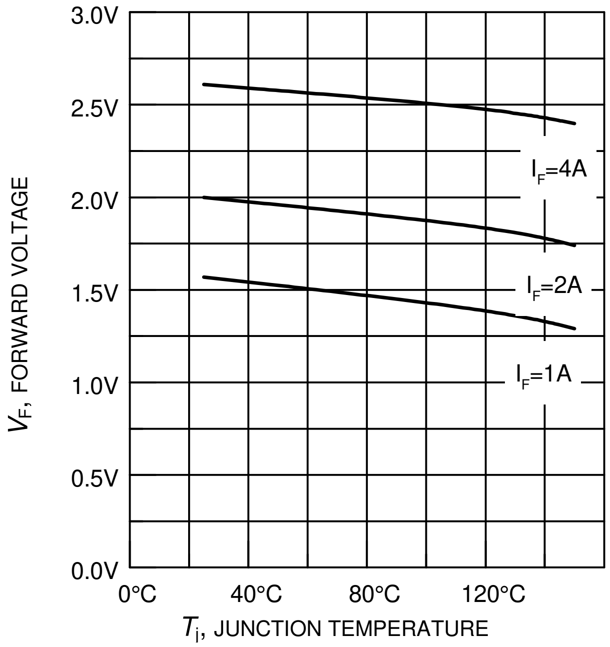
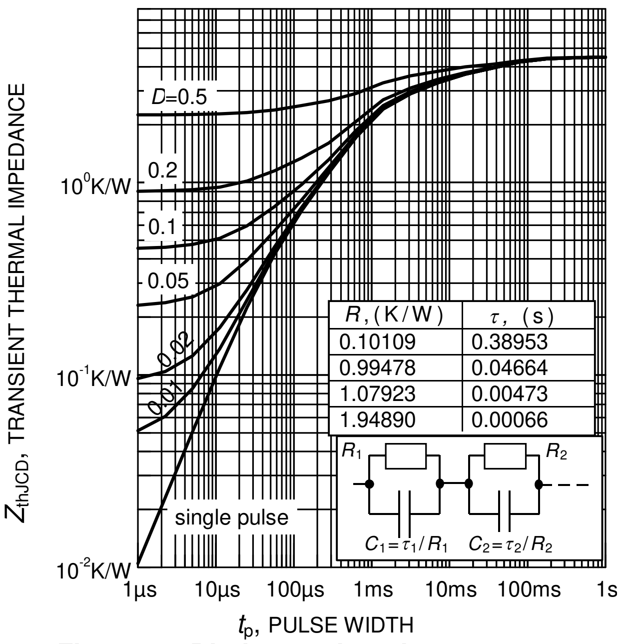


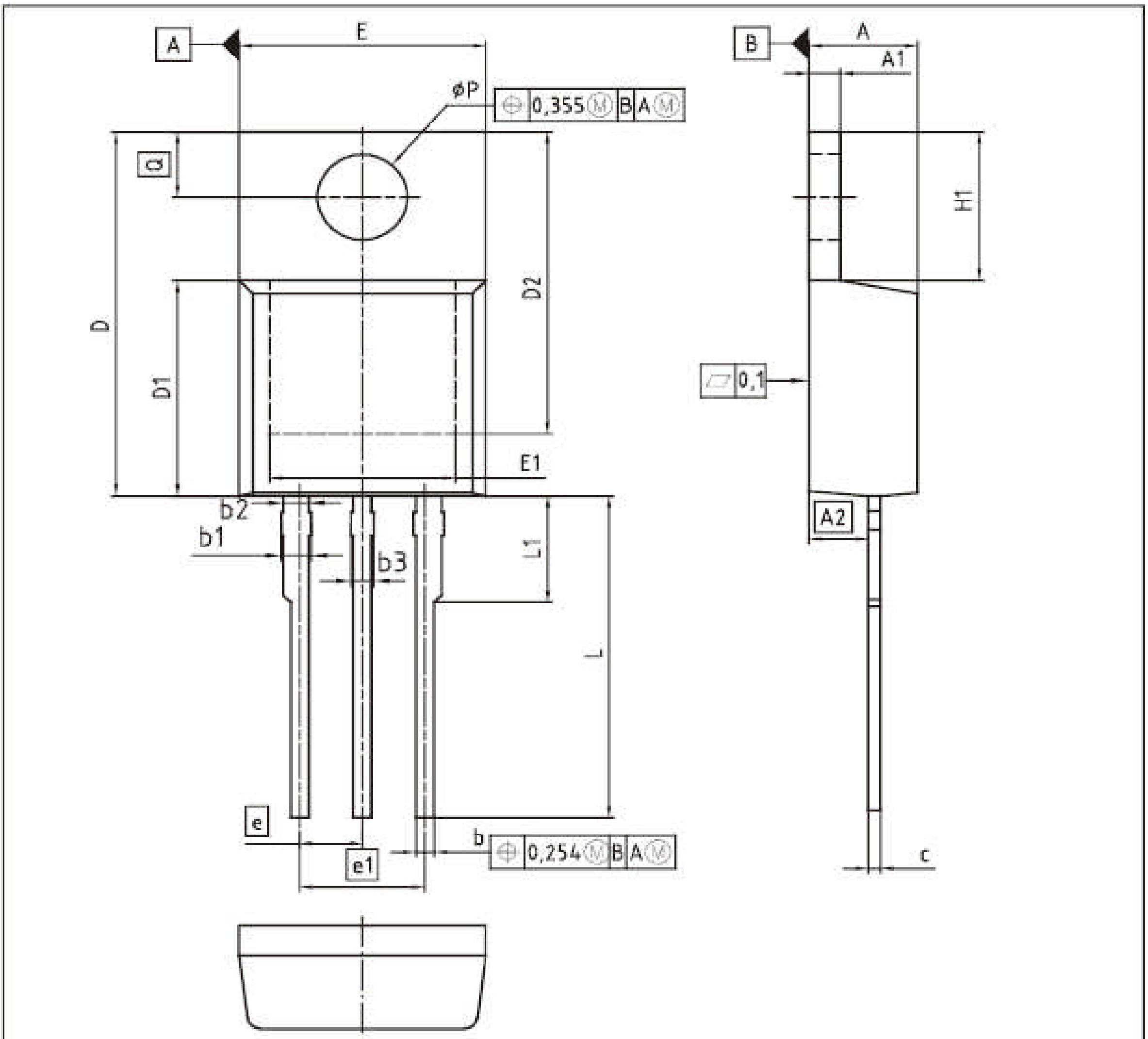
Figure 26. Typical diode forward voltage as a function of junction temperature



R, (K/W)	τ, (s)
0.10109	0.38953
0.99478	0.04664
1.07923	0.00473
1.94890	0.00066

Figure 27. Diode transient thermal impedance as a function of pulse width
($D = t_p / T$)

PG-TO220-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
øP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

DOCUMENT NO.
Z8B00003318

SCALE 0 2.5 5mm

EUROPEAN PROJECTION

ISSUE DATE
30-07-2009

REVISION
06

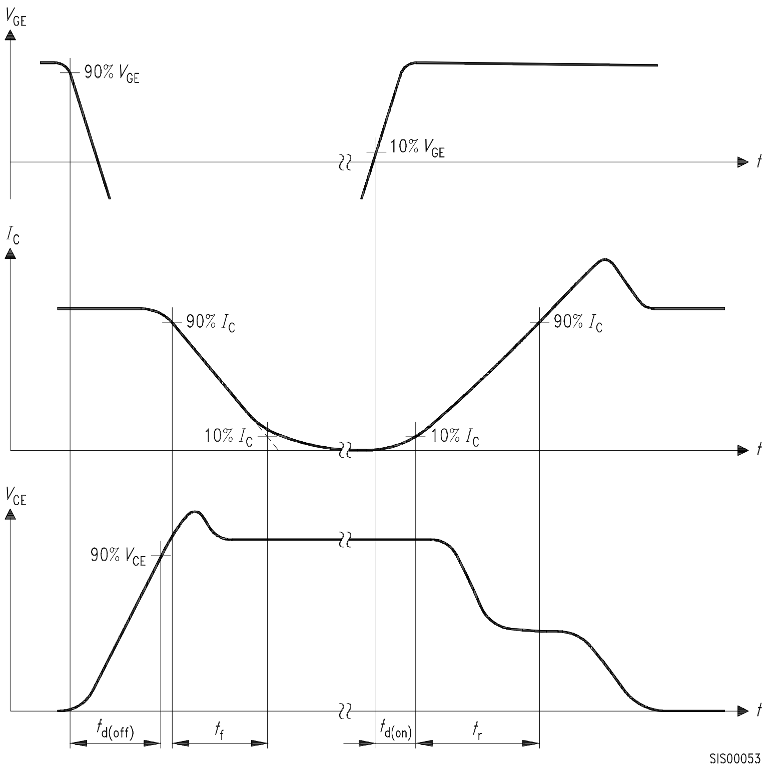


Figure A. Definition of switching times

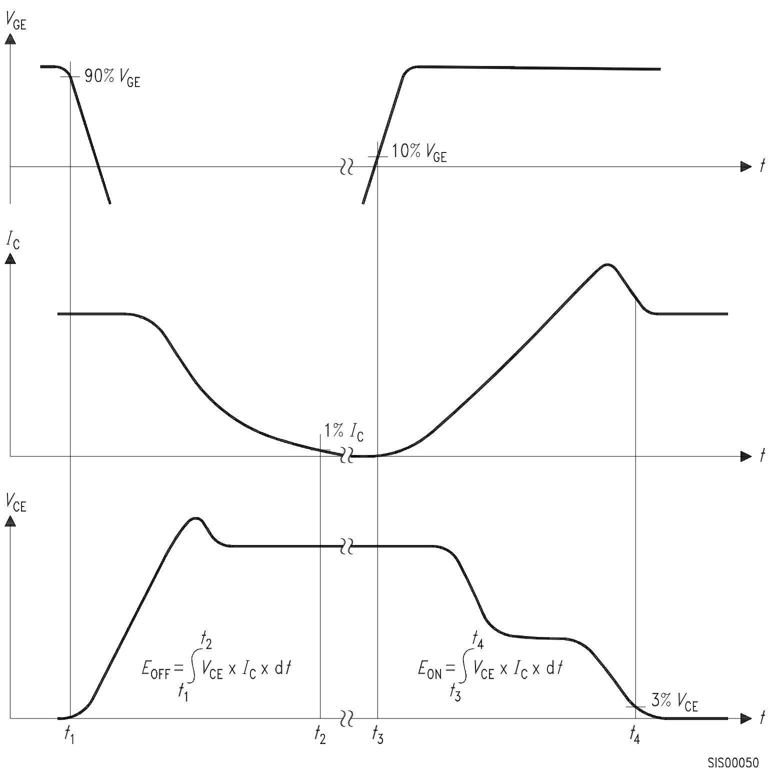


Figure B. Definition of switching losses

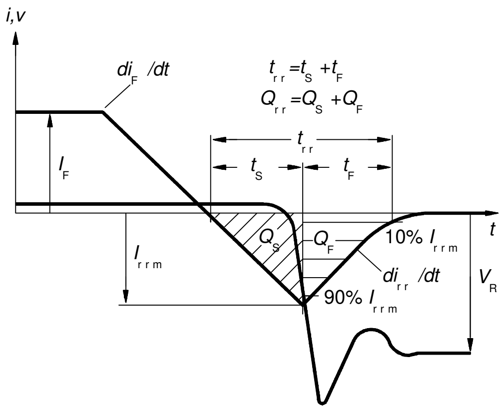


Figure C. Definition of diodes switching characteristics

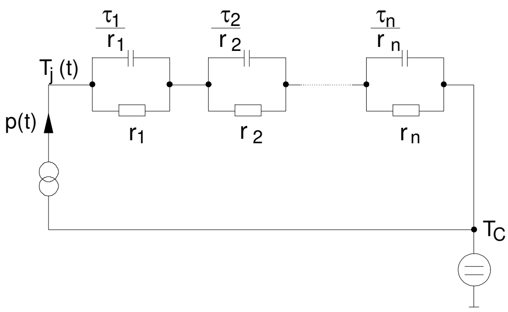


Figure D. Thermal equivalent circuit

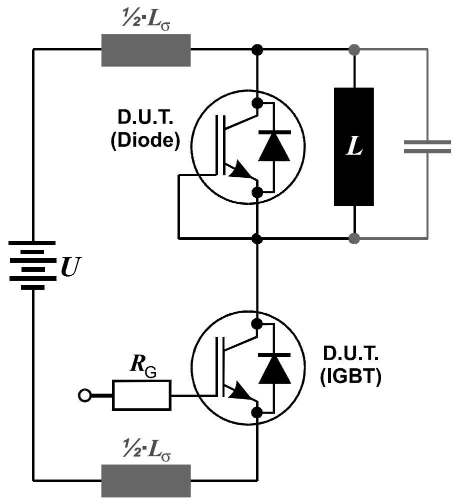


Figure E. Dynamic test circuit
Leakage inductance L_σ=180nH, and stray capacity C_σ =40pF.

Published by
Infineon Technologies AG
81726 Munich, Germany

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (**www.infineon.com**).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.
The Infineon Technologies component described in this Data Sheet may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support, automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.